INTEGRATED CIRCUITS

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

HEF4060B MSI

14-stage ripple-carry binary counter/divider and oscillator

Product specification
File under Integrated Circuits, IC04

January 1995





14-stage ripple-carry binary counter/divider and oscillator

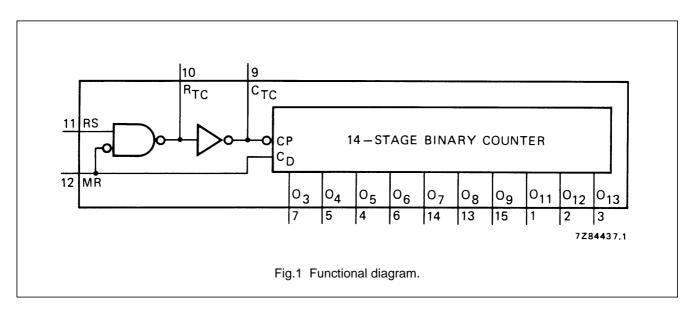
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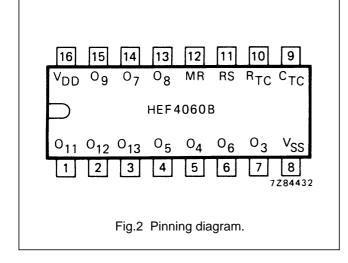
DESCRIPTION

The HEF4060B is a 14-stage ripple-carry binary counter/divider and oscillator with three oscillator terminals (RS, R_{TC} and C_{TC}), ten buffered outputs (O $_3$ to O $_9$ and O $_{11}$ to O $_{13}$) and an overriding asynchronous master reset input (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may

be replaced by an external clock signal at input RS. The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (O_3 to O_9 and O_{11} to O_{13} = LOW), independent of other input conditions.

Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.





PINNING

MR	master reset
RS	clock input/oscillator pin
R_{TC}	oscillator pin
<u>C</u>	ovtornal consoiter connect

C_{TC} external capacitor connection

 O_3 to O_9 O_{11} to O_{13} counter outputs

HEF4060BP(N): 16-lead DIL; plastic (SOT38-1)

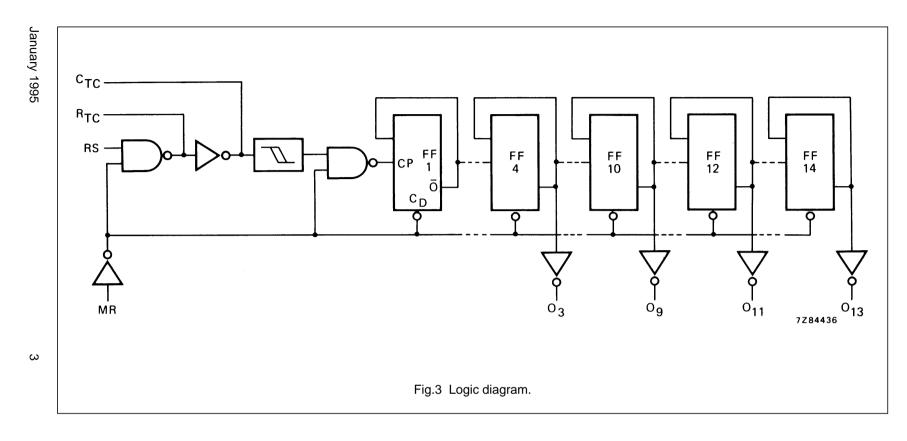
HEF4060BD(F): 16-lead DIL; ceramic (cerdip) (SOT74)

HEF4060BT(D): 16-lead SO; plastic (SOT109-1)

(): Package Designator North America

FAMILY DATA, I_{DD} LIMITS category MSI

See Family Specifications



Philips Semiconductors Product specification

14-stage ripple-carry binary counter/divider and oscillator

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AC CHARACTERISTICS

 V_{SS} = 0 V; T_{amb} = 25 °C; C_L = 50 pF; input transition times \leq 20 ns

	V _{DD}	SYMBOL	MIN.	TYP.	MAX.		TYPICAL EXTRAPOLATION FORMULA
Propagation delays							
$RS \to O_3$	5			210	420	ns	183 ns + (0,55 ns/pF) C _L
HIGH to LOW	10	t _{PHL}		80	160	ns	69 ns + (0,23 ns/pF) C _L
	15			50	100	ns	42 ns + (0,16 ns/pF) C _L
	5			210	420	ns	183 ns + (0,55 ns/pF) C _L
LOW to HIGH	10	t _{PLH}		80	160	ns	69 ns + (0,23 ns/pF) C _L
	15			50	100	ns	42 ns + (0,16 ns/pF) C _L
$O_n \rightarrow O_{n+1}$	5			25	50	ns	
HIGH to LOW	10	t _{PHL}		10	20	ns	
	15			6	12	ns	
	5			25	50	ns	
LOW to HIGH	10	t _{PLH}		10	20	ns	
	15			6	12	ns	
$MR \to O_n$	5			100	200	ns	73 ns + (0,55 ns/pF) C _L
HIGH to LOW	10	t _{PHL}		40	80	ns	29 ns + (0,23 ns/pF) C _L
	15			30	60	ns	22 ns + (0,16 ns/pF) C _L
Output transition	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
times	10	t _{THL}		30	60	ns	9 ns + (0,42 ns/pF) C _L
HIGH to LOW	15			20	40	ns	6 ns + (0,28 ns/pF) C _L
	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
LOW to HIGH	10	t _{TLH}		30	60	ns	9 ns + (0,42 ns/pF) C _L
	15			20	40	ns	6 ns + (0,28 ns/pF) C _L
Minimum clock pulse	5		120	60		ns	
width input RS	10	t _{WRSH}	50	25		ns	
HIGH	15		30	15		ns	
Minimum MR pulse	5		50	25		ns	
width; HIGH	10	t _{WMRH}	30	15		ns	
	15		20	10		ns	
Recovery time	5		160	80		ns	
for MR	10	t _{RMR}	80	40		ns	
	15		60	30		ns	
Maximum clock pulse	5		4	8		MHz	
frequency input RS	10	f _{max}	10	20		MHz	
	15		15	30		MHz	

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	V _{DD}	TYPICAL FORMULA FOR P (μW) ⁽¹⁾			
Dynamic power dissipation	5	$700 f_i + f_o C_L V_{DD}^2$			
per package	10	$3\ 300\ f_i + f_o C_L V_{DD}^2$			
(P)	15	$8\ 900\ f_i + f_0C_LV_{DD}^2$			
Total power dissipation	5	$700 f_{osc} + f_o C_L V_{DD}^2 + 2 C_t V_{DD}^2 f_{osc} + 690 V_{DD}$			
when using the	10	$3\ 300\ f_{osc} + f_o C_L V_{DD}^2 + 2C_t V_{DD}^2 f_{osc} + 6\ 900\ V_{DD}$			
on-chip oscillator (P)	15	$8\ 900\ f_{osc}\ +\ f_o C_L V_{DD}^2\ +\ 2C_t V_{DD}^2 f_{osc}\ +\ 22\ 000\ V_{DD}$			

Notes

1. where:

 f_i = input frequency (MHz)

 $f_o = output frequency (MHz)$

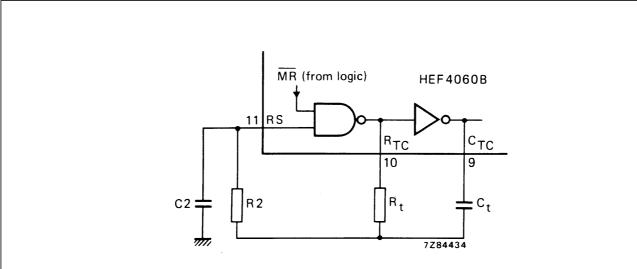
C_L = load capacitance (pF)

V_{DD} = supply voltage (V)

C_t = timing capacitance (pF)

 f_{osc} = oscillator frequency (MHz)

RC oscillator



Typical formula for oscillator frequency:

$$f_{osc} = \frac{1}{2,3 \times R_t \times C_t}$$

Fig.4 External component connection for RC oscillator.

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Timing component limitations

The oscillator frequency is mainly determined by R_tC_t , provided $R_t << R2$ and $R2C2 << R_tC_t$. The function of R2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the LOCMOS 'ON' resistance in series with it, which typically is $500~\Omega$ at V_{DD} = 5~V, $300~\Omega$ at V_{DD} = 10~V and $200~\Omega$ at V_{DD} = 15~V.

The recommended values for these components to maintain agreement with the typical oscillation formula are:

 $C_t \geq 100 \text{ pF, up to any practical value,} \\ 10 \text{ } k\Omega \leq R_t \leq 1 \text{ } M\Omega.$

Typical crystal oscillator circuit

In Fig.5, R2 is the power limiting resistor. For starting and maintaining oscillation a minimum transconductance is necessary.

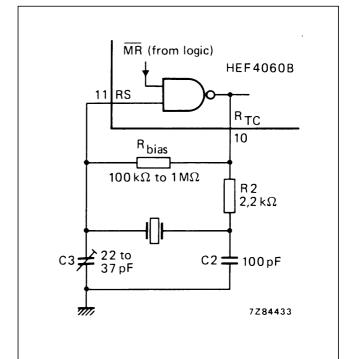


Fig.5 External component connection for crystal oscillator.

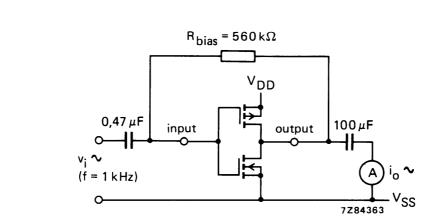


Fig.6 Test set-up for measuring forward transconductance $g_{fs} = di_o/dv_i$ at v_o is constant (see also graph Fig.7); MR = LOW.

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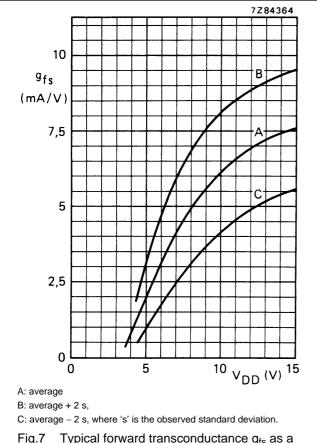


Fig.7 Typical forward transconductance g_{fs} as a function of the supply voltage at T_{amb} = 25 °C.

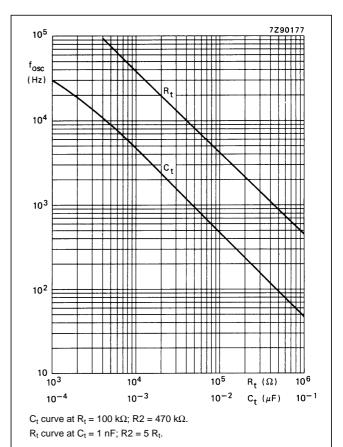


Fig.8 RC oscillator frequency as a function of R_t and C_t at V_{DD} = 5 to 15 V; T_{amb} = 25 °C.

